

Silicon N-Channel Power MOSFET

General Description:

The HMR20N06L uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications. The package form is TO-252, which accords with the RoHS standard.

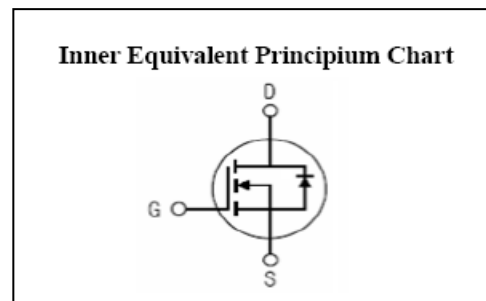
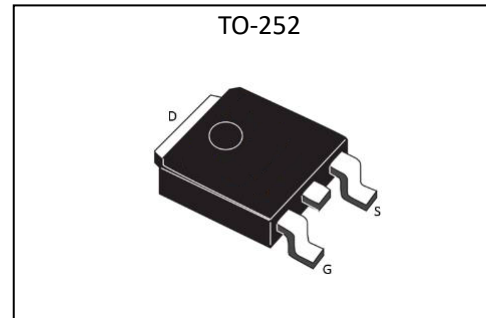
Features:

- Fast Switching
- Low Gate Charge and $R_{DS(ON)}$
- Low Reverse transfer capacitances
- 100% Single Pulse avalanche energy Test

Applications:

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

V_{DSS}	60	V
I_D	20	A
P_D	45	W
$R_{DS(ON).TYP.}$	27	m Ω



Absolute (Tc= 25°C unless otherwise specified):

Symbol	Parameter	Rating	Units
V_{DSS}	Drain-to-Source Voltage	60	V
I_D	Continuous Drain Current	20	A
	Continuous Drain Current $T_C = 100^\circ\text{C}$	14	A
I_{DM}	Pulsed Drain Current	60	A
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}^{a2}	Single Pulse Avalanche Energy	72	mJ
E_{AR}^{a1}	Avalanche Energy ,Repetitive	18	mJ
I_{AR}^{a1}	Avalanche Current	11	A
dv/dt^{a3}	Peak Diode Recovery dv/dt	5.0	V/ns
P_D	Power Dissipation	45	W
T_J, T_{stg}	Operating Junction and Storage Temperature Range	175, -55 to 175	$^\circ\text{C}$
T_L	Maximum Temperature for Soldering	300	$^\circ\text{C}$

Electrical Characteristics (Tc= 25°C unless otherwise specified):

OFF Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
V _{DSS}	Drain to Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	60	--	--	V
ΔBV _{DSS} /ΔT _J	Bvdss Temperature Coefficient	I _D =250uA, Reference 25°C	--	0.1	--	V/°C
I _{DSS}	Drain to Source Leakage Current	V _{DS} =60V, V _{GS} =0V, T _a =25°C	--	--	1	μA
		V _{DS} =48V, V _{GS} =0V, T _a =125°C	--	--	250	
I _{GSS(F)}	Gate to Source Forward Leakage	V _{GS} = +20V	--	--	1	μA
I _{GSS(R)}	Gate to Source Reverse Leakage	V _{GS} = -20V	--	--	-1	μA

ON Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
R _{DS(ON)}	Drain-to-Source On-Resistance	V _{GS} =10V, I _D =20A	--	27	35	mΩ
V _{GS(TH)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1.0	1.7	2.5	V
Pulse width tp ≤ 380μs, δ ≤ 2%						

Dynamic Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
g _{fs}	Forward Transconductance	V _{DS} =5V, I _D =5A	11	--	--	S
C _{iss}	Input Capacitance	V _{GS} =0V V _{DS} =30V f=1.0MHz	--	500	--	pF
C _{oss}	Output Capacitance		--	60	--	
C _{rss}	Reverse Transfer Capacitance		--	25	--	

Resistive Switching Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
t _{d(ON)}	Turn-on Delay Time	I _D =2A, V _{DD} =30V V _{GS} =10V, R _G =3.0Ω	--	5	--	ns
t _r	Rise Time		--	2.6	--	
t _{d(OFF)}	Turn-Off Delay Time		--	2.3	--	
t _f	Fall Time		--	5.5	--	
Q _g	Total Gate Charge	I _D =4.5A, V _{DD} =30V, V _{GS} =10V	--	47	--	nC
Q _{gs}	Gate to Source Charge		--	6	--	
Q _{gd}	Gate to Drain ("Miller") Charge		--	14	--	

Source-Drain Diode Characteristics						
Symbol	Parameter	Test Conditions	Rating			Units
			Min.	Typ.	Max.	
I_S	Continuous Source Current (Body Diode)		--	--	20	A
I_{SM}	Maximum Pulsed Current (Body Diode)		--	--	60	A
V_{SD}	Diode Forward Voltage	$I_S=20A, V_{GS}=0V$	--	--	1.5	V
t_{rr}	Reverse Recovery Time	$I_S=10A, T_j = 25^\circ C$	--	35	--	ns
Q_{rr}	Reverse Recovery Charge	$di_F/dt=100A/us, V_{GS}=0V$	--	50	--	nC

Pulse width $t_p \leq 380\mu s, \delta \leq 2\%$

Symbol	Parameter	Typ.	Units
$R_{\theta JA}$	Junction-to-Ambient	3.3	$^\circ C/W$

a1: Repetitive rating; pulse width limited by maximum junction temperature

a2: EAS condition : $T_j=25, V_{DD}=30V, V_G=10V, L=0.5mH, R_g=25\Omega$

a3: $I_{SD}=10A, di/dt \leq 100A/us, V_{DD} \leq BV_{DS}, Start T_j=25^\circ C$

Test Circuit and Waveform

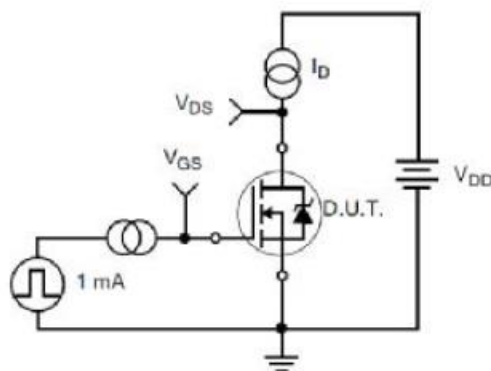


Figure 17. Gate Charge Test Circuit

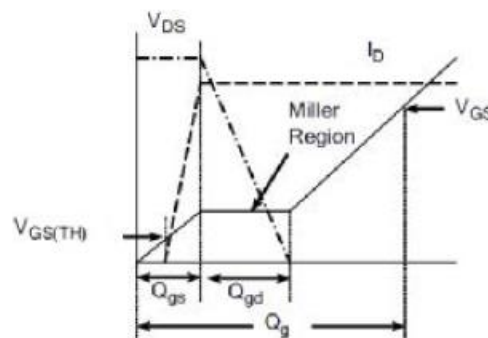


Figure 18. Gate Charge Waveform

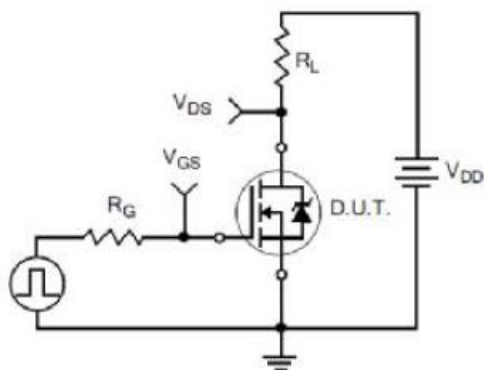


Figure 19. Resistive Switching Test Circuit

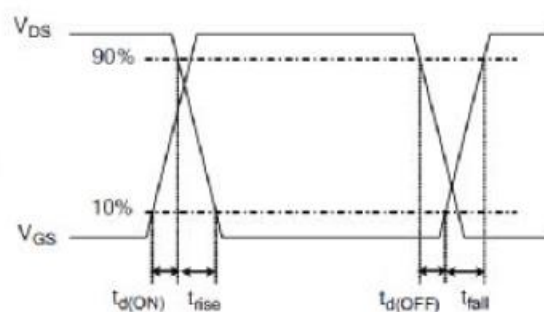


Figure 20. Resistive Switching Waveforms

Characteristics Curve:

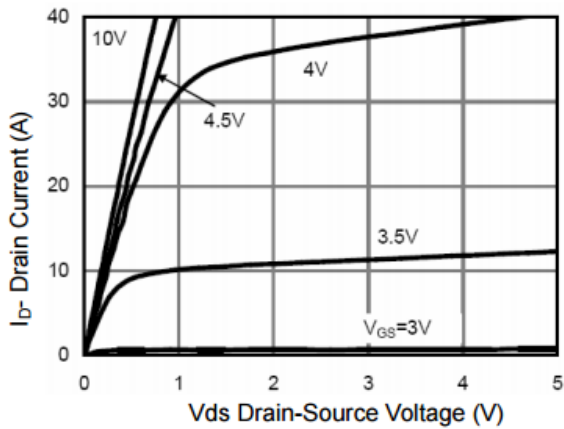


Figure 1 Output Characteristics

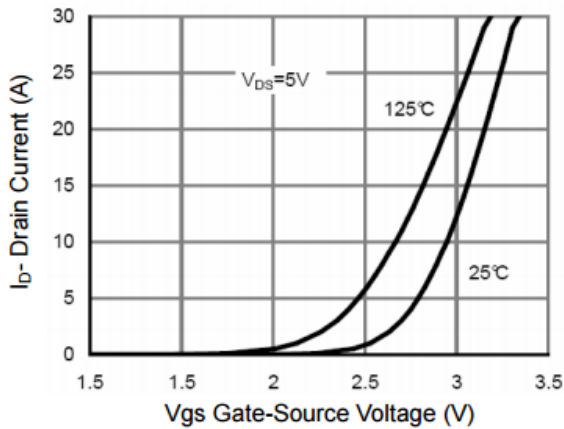


Figure 2 Transfer Characteristics

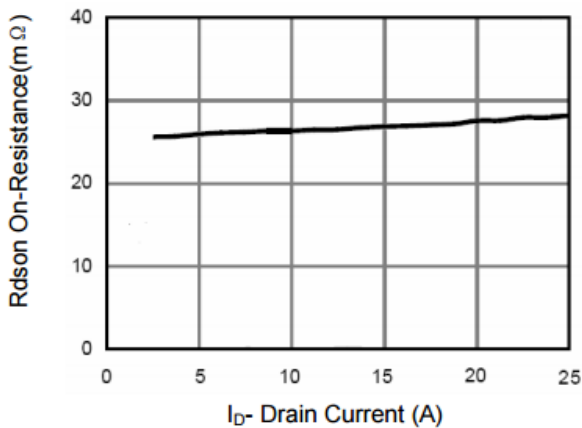


Figure 3 Rdson- Drain Current

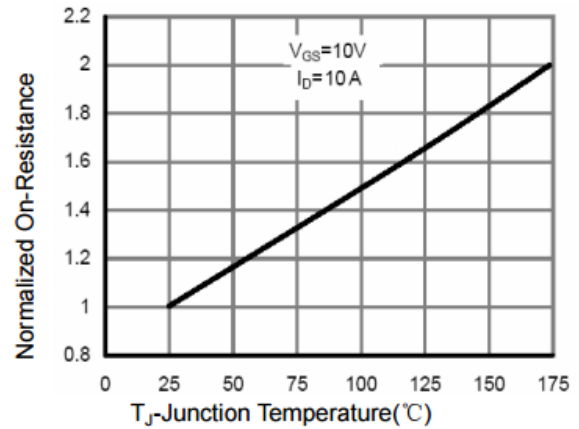


Figure 4 Rdson-Junction Temperature

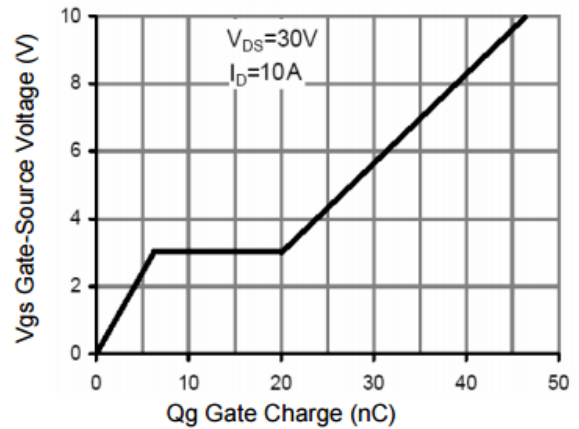


Figure 5 Gate Charge

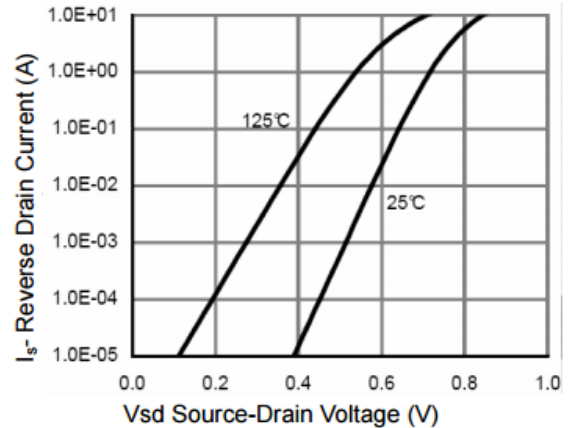


Figure 6 Source- Drain Diode Forward

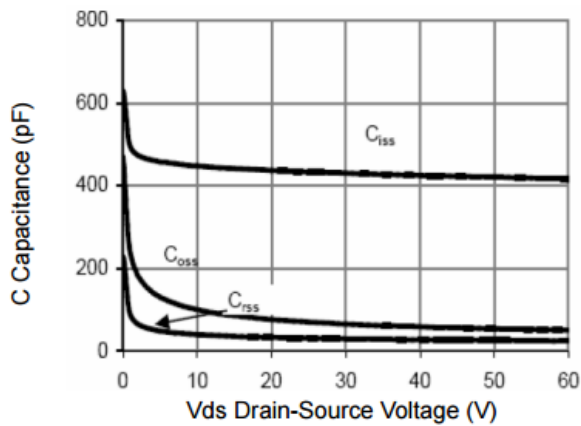


Figure 7 Capacitance vs Vds

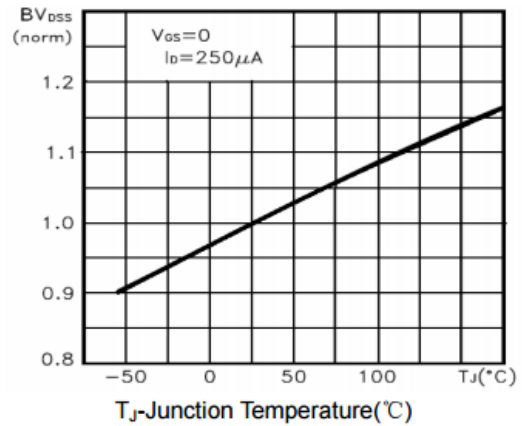


Figure 9 BV_{DSS} vs Junction Temperature

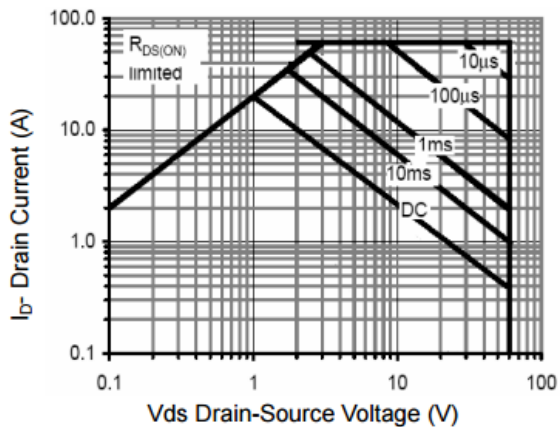


Figure 8 Safe Operation Area

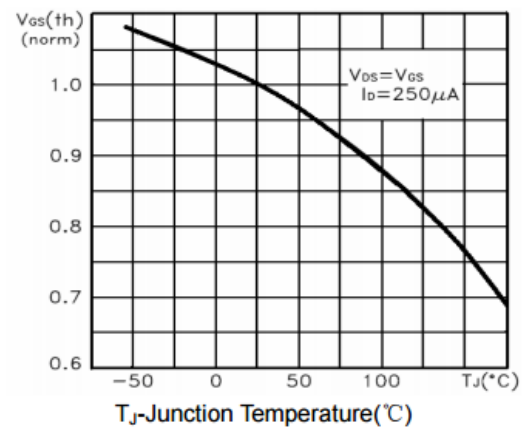


Figure 10 $V_{GS(th)}$ vs Junction Temperature

